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- Low $r_{DS(on)} \dots 5 \Omega$ Typical
- Avalanche Energy ... 30 mJ
- Eight Power DMOS-Transistor Outputs of 150-mA Continuous Current
- 500-mA Typical Current-Limiting Capability
- Output Clamp Voltage . . . 50 V
- Low Power Consumption

description

The TPIC6B273 is a monolithic, high-voltage, medium-current, power logic octal D-type latch with DMOS-transistor outputs designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other medium-current or high-voltage loads.

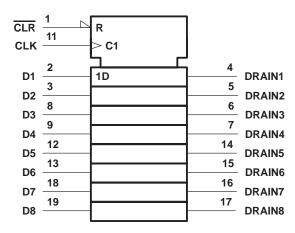
The TPIC6B273 contains eight positive-edgetriggered D-type flip-flops with a direct clear input. Each flip-flop features an open-drain power DMOS-transistor output.

When clear (CLR) is high, information at the D inputs meeting the setup time requirements is transferred to the DRAIN outputs on the positivegoing edge of the clock (CLK) pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock input (CLK) is at either the high or low level, the D input signal has no effect at the output. An asynchronous CLR is provided to turn all eight DMOS-transistor outputs off. When data is low for a given output, the DMOS-transistor output is off. When data is high, the DMOS-transistor output has sink-current capability.

Outputs are low-side, open-drain DMOS transistors with output ratings of 50 V and 150-mA continuous sink-current capability. Each output provides a 500-mA typical current limit at $T_C = 25^{\circ}$ C. The current limit decreases as the junction temperature increases for additional device protection.

DW OR N PACKAGE (TOP VIEW)							
CLR D1 D2 DRAIN1 DRAIN2 DRAIN3 DRAIN4 D3 D4 GND	1 2 3 4 5 6 7 8 9 10	20 19 18 17 16 15 14 13 12	V _{CC} D8 D7 DRAIN8 DRAIN7 DRAIN6 DRAIN5 D6 D5				

logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Standard 91-1984 and IEC Publication 617-12.

FUNCTION TABLE (each channel)									
	INPUTS OUTPUT								
CLR	CLK	D	DRAIN						
L	Х	Х	Н						
Н	\uparrow	Н	L						
н	\uparrow	L	н						
н	L	Х	Latched						

H = high level, L = low level, X = irrelevant

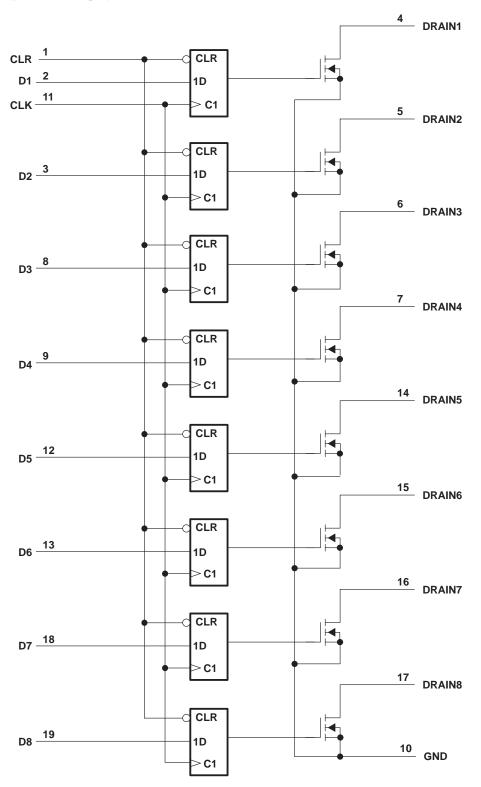
The TPIC6B273 is characterized for operation over the operating case temperature range of -40°C to 125°C.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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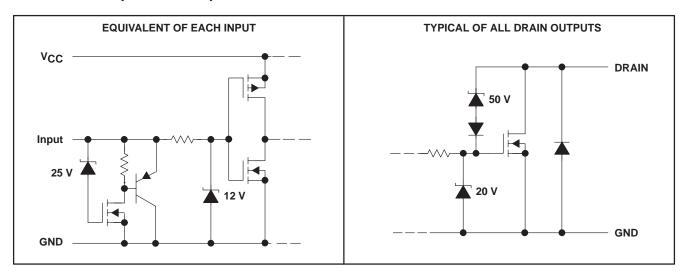
logic diagram (positive logic)





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schematic of inputs and outputs



absolute maximum ratings over recommended operating case temperature range (unless otherwise noted) $\!\!\!\!^\dagger$

Logic supply voltage, V _{CC} (see Note 1)	
Logic input voltage range, V _I	$\dots \dots \dots \dots -0.3$ V to 7 V
Power DMOS drain-to-source voltage, V _{DS} (see Note 2)	50 V
Continuous source-to-drain diode anode current	
Pulsed source-to-drain diode anode current (see Note 3)	1 A
Pulsed drain current, each output, all outputs on, I_D , $T_C = 25^{\circ}C$ (see Note 3)	500 mA
Continuous drain current, each output, all outputs on, I_D , $T_C = 25^{\circ}C$	150 mA
Peak drain current single output, I _{DM} ,T _C = 25°C (see Note 3)	500 mA
Single-pulse avalanche energy, E _{AS} (see Figure 4)	
Avalanche current, I _{AS} (see Note 4)	500 mA
Continuous total dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T ₁	40°C to 150°C
Operating case temperature range, T _C	40°C to 125°C
Storage temperature range	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to GND.

2. Each power DMOS source is internally connected to GND.

3. Pulse duration \leq 100 μ s and duty cycle \leq 2%.

4. DRAIN supply voltage = 15 V, starting junction temperature (T_{JS}) = 25°C, L = 200 mH, I_{AS} = 0.5 A (see Figure 4).

DISSIPATION RATING TABLE

PACKAGE	T _C ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _C = 25°C	T _C = 125°C POWER RATING
DW	1389 mW	11.1 mW/°C	278 mW
N	1050 mW	10.5 mW/°C	263 mW



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recommended operating conditions

	MIN	MAX	UNIT
Logic supply voltage, V _{CC}	4.5	5.5	V
High-level input voltage, VIH	0.85 V _{CC}		V
Low-level input voltage, VIL		0.15 V _{CC}	V
Pulsed drain output current, $T_C = 25^{\circ}C$, $V_{CC} = 5 V$ (see Notes 3 and 5)	-500	500	mA
Setup time, D high before CLK [↑] , t _{SU} (see Figure 2)	20		ns
Hold time, D high after CLK [↑] , t _h (see Figure 2)	20		ns
Pulse duration, t _W (see Figure 2)	40		ns
Operating case temperature, T _C	-40	125	°C

electrical characteristics, V_{CC} = 5 V, T_{C} = 25°C (unless otherwise noted)

	PARAMETER		TEST CONDITIC	DNS	MIN	TYP	MAX	UNIT
V _{(BR)DSX}	Drain-to-source breakdown voltage	I _D = 1 mA			50			V
V _{SD}	Source-to-drain diode forward voltage	I _F = 100 mA				0.85	1	V
Iн	High-level input current	V _{CC} = 5.5 V,	$V_{I} = V_{CC}$				1	μA
۱ _{IL}	Low-level input current	V _{CC} = 5.5 V,	$V_{I} = 0$				-1	μA
laa			All outputs off			20	100	
lcc	Logic supply current	$V_{CC} = 5.5 V$	All outputs on			150	300	μA
IN	Nominal current	V _{DS(on)} = 0.5 V, See Notes 5, 6, a		T _C = 85°C,		90		mA
I	Off state drain surrent	V _{DS} = 40 V,	V _{CC} = 5.5 V			0.1	5	
IDSX	Off-state drain current	V _{DS} = 40 V,	V _{CC} = 5.5 V,	T _C = 125°C		0.15	8	μA
		I _D = 100 mA,	V _{CC} = 4.5 V			4.2	5.7	
^r DS(on)	Static drain-to-source on-state resistance	I _D = 100 mA, T _C = 125°C	V _{CC} = 4.5 V,	See Notes 5 and 6 and Figures 6 and 7		6.8	9.5	Ω
		I _D = 350 mA,	V _{CC} = 4.5 V	1		5.5	8	

switching characteristics, V_{CC} = 5 V, T_C = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
^t PLH	Propagation delay time, low-to-high-level output from CLK			150		ns	
^t PHL	Propagation delay time, high-to-low-level output from CLK	C _L = 30 pF, I _D = 100 mA,		90		ns	
tr	Rise time, drain output	See Figures 1, 2, and 8		200		ns	
t _f	Fall time, drain output			200		ns	
ta	Reverse-recovery-current rise time	I _F = 100 mA, di/dt = 20 A/µs,		100		ns	
t _{rr}	Reverse-recovery time	See Notes 5 and 6 and Figure 3		300		115	

NOTES: 3. Pulse duration \leq 100 μs and duty cycle \leq 2%.

5. Technique should limit $T_J - T_C$ to 10°C maximum.

6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at $T_C = 85^{\circ}C$.

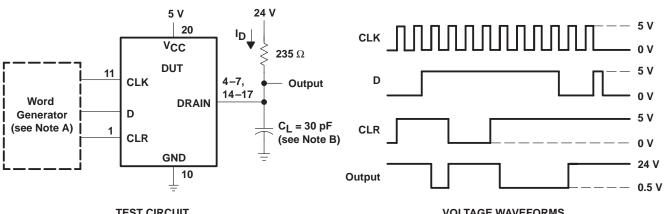


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thermal resistance

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT		
Paul	Thermal registeres, junction to embient	DW package	All 8 outputs with equal power		90	00 AM	
R _{θJA}	Thermal resistance, junction-to-ambient	N package	All o oulputs with equal power		95	°C/W	

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

VOLTAGE WAVEFORMS



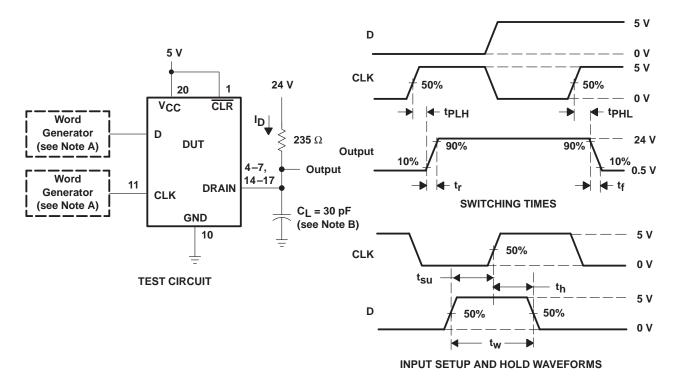
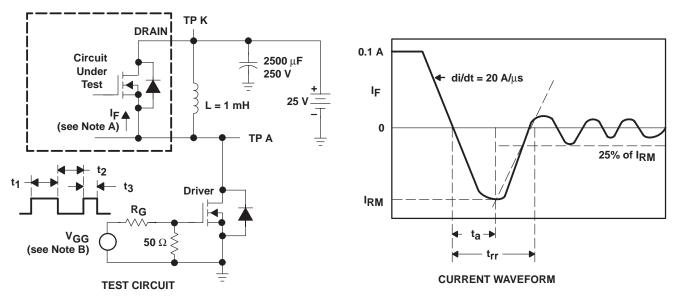


Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

- NOTES: A. The word generator has the following characteristics: $t_f \le 10$ ns, $t_f \le 10$ ns, $t_W = 300$ ns, pulsed repetition rate (PRR) = 5 KHz, Z_O = 50 Ω.
 - B. CL includes probe and jig capacitance.



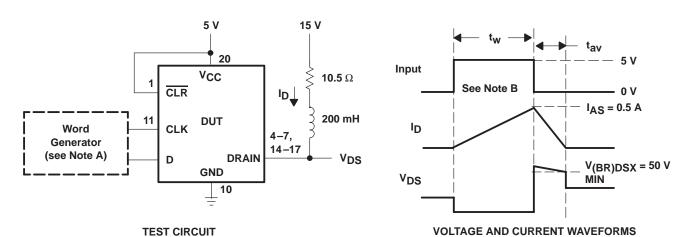
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PARAMETER MEASUREMENT INFORMATION

- NOTES: A. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.
 - B. The V_{GG} amplitude and R_G are adjusted for di/dt = 20 A/ μ s. A V_{GG} double-pulse train is used to set I_F = 0.1 A, where t₁ = 10 μ s, t₂ = 7 μ s, and t₃ = 3 μ s.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-to-Drain Diode



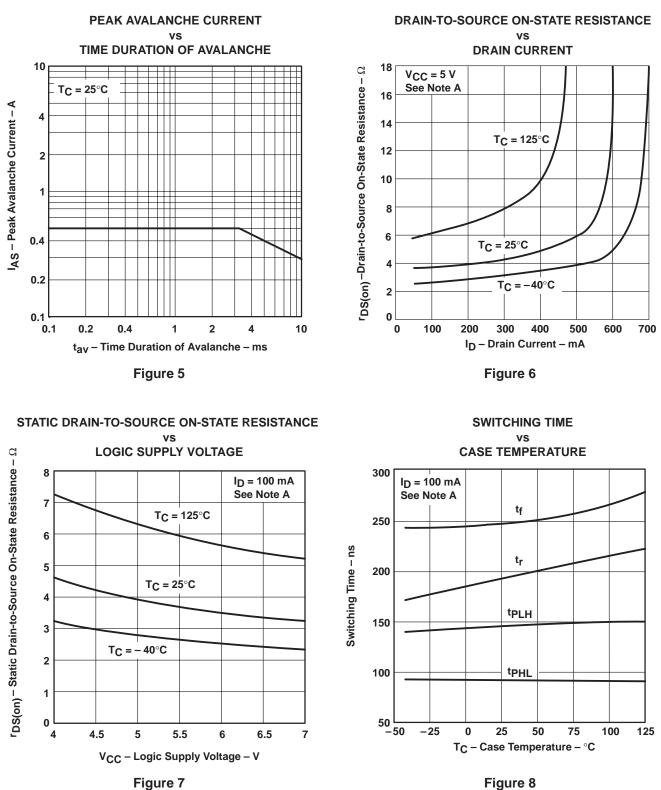
NOTES: A. The word generator has the following characteristics: $t_{f} \le 10$ ns, $t_{f} \le 10$ ns, $Z_{O} = 50 \Omega$. B. Input pulse duration, t_{W} , is increased until peak current $I_{AS} = 0.5$ A. Energy test is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 30$ mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms



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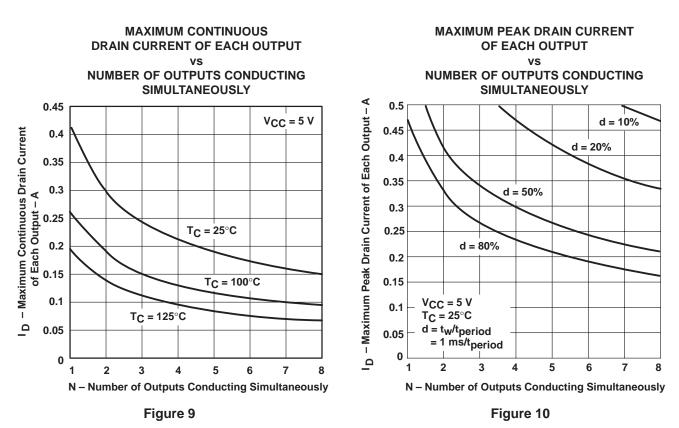
TYPICAL CHARACTERISTICS



NOTE C: Technique should limit $T_J - T_C$ to 10°C maximum.



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THERMAL INFORMATION





11-Apr-2013

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
TPIC6B273DW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6B273	Samples
TPIC6B273DWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		TPIC6B273	Samples
TPIC6B273DWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6B273	Samples
TPIC6B273DWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		TPIC6B273	Samples
TPIC6B273N	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 125	TPIC6B273N	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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PACKAGE OPTION ADDENDUM

11-Apr-2013

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC6B273DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

4-Jan-2013



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC6B273DWR	SOIC	DW	20	2000	367.0	367.0	45.0

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



DW0020A

EXAMPLE BOARD LAYOUT

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DW0020A

EXAMPLE STENCIL DESIGN

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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